Amendments to the Specification

Paragraph at page 6, line 28 to page 7, line 9:

A specific example of a first embodiment of a magnetron sputter reactor 40 [[20]] of the invention is illustrated in the schematic cross-sectional view of FIG. 4. The fairly conventional portion of the reactor 40 will be described first. Cha et al. have described details of some of the components in US Patent Application 09/910,585, filed July 20, 2001, now abandoned, published as Publication No. US-2003-0015421-A1, and incorporated herein by reference in its entirety. The reactor 40 includes a vacuum processing chamber principally formed of a chamber body 42 and an adapter 44 formed generally symmetrically about a central axis 46 and electrically grounded. A vacuum pumping system 48 is connected to the chamber through a pumping port 50 and can pump the chamber to a base pressure in the range of 10^{-8} Torr. However, an argon gas source 52 supplies argon into the chamber through a mass flow controller 54 to act as a sputtering working gas. Typical argon pressures used in sputtering are in the range of 0.5 to 5 milliTorr.